

<b>Notice of References Cited</b>			Application/Control No. 10/063,128	Applicant(s)/Patent Under Reexamination LIANG ET AL.	
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	C	US-6225167	05-2001	Yu et al.	438/275
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	M	US-			

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#### NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	S.L. Wu et al. Suppression of the Boron Penetration Induced Si/SiO <sub>2</sub> Interface Degradation by Using a Stacked-Amorphous-Silicon Film as the Gate Structure for pMOSFET. IEEE 1994, pp. 160-162.
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\*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)  
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.